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PTO/SB/08a-b (08-03)

Substitute for form 1449A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	Not Yet Assigned 10/777,684
(Use as many sheets as necessary)				Filing Date	Concurrently Herewith
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2823
				Examiner Name	Not Yet Assigned H. LEE
Sheet	1	of	14	Attorney Docket Number	M4065.0699/P699-B

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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** <i>JL</i>	BC	00/48196 A1	08/2000	WIPO		

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<i>John</i>	CA	Axon Technologies Corporation, "Programmable Metallization Cell (PMC)," pp.1-6 (pre 2000).
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<i>Lee</i>	CC	J.N. Helbert, et al., "Intralevel Hybrid Resist Process with Submicron Capability," SPIE, Vol. 333, pp. 24-29. 1982.

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**Lee	BD	WO 97/48032	12/1997	WIPO	
**Lee	BE	WO 99/28914	06/1999	WIPO	

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**Lee	CF	Hirose et al., "Polarity-Dependent Memory Switching and Behavior of Ag Dendrite in Ag-Photodoped As ₂ S ₃ Films," 47 J. Appl. Phys., No. 6, pp. 2767-2772, June 1976.			

Lee May Lee

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** Lee	AL1	6,297,170	10/2001	Gabriel et al.	
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Karen May Lee *6/29/2005*

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**	AD2	6,388,324	05/2002	Kozicki et al.	
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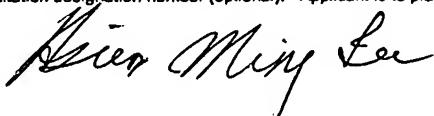
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Lee	CC2	Boolchand, et al., "Onset of Rigidity in Steps in Chalcogenide Glasses," Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, pp. 97-132, 2001.				
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**	CJ2	Bresser, et al., "Intrinsically Broken Chalcogen Chemical Order in Stoichiometric Glasses," Journal de Physique, 42, C4-193-C4-196, 1981.				
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**	CM2	Chatterjee, et al., "Current-controlled Negative-resistance Behavior and Memory Switching in Bulk As-Te-Se Glasses," J. Phys. D: Appl. Phys., 27, 2624-2627, 1994.				
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**	CP2	Chen, et al., "Effect of Si ₃ N ₄ on Chemical Durability of Chalcogenide Glass," J. Non-Cryst. Solids, 220, 249-253, 1997.				
**	CQ2	Cohen, et al., "A Model for an Amorphous Semiconductor Memory Device," J. Non-Cryst. Solids 8-10, 885-891, 1972.				
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** <i>Lee</i>	CW2	den Boer, "Threshold Switching in Hydrogenated Amorphous Silicon," Appl. Phys. Lett., 40, 812-813, 1982.			
**	CX2	Drusdau, et al., "The Hydrogenated Amorphous Silicon/nanodisperse Metal (SIMAL) System-Films of Unique Electronic Properties," J. Non-Cryst. Solids, 198-200, 829-832, 1996.			
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**	CR3	Guin, et al., "Indentation Creep of Ge-Se Chalcogenide Glasses Below Tg: Elastic Recovery and Non-Newtonian Flow," J. Non-Cryst. Solids, 298, 260-269, 2002.			
**	CS3	Guin, et al., "Hardness, Toughness, and Scratchability of Germanium-selenium Chalcogenide Glasses," J. Am. Ceram. Soc., 85, 1545-52, 2002.			
**	CT3	Gupta, "On Electrical Switching and Memory Effects in Amorphous Chalcogenides," J. Non-Cryst. Sol., 3, 148-154, 1970.			
**	CU3	Haberland, et al., "New Experiments on the Charge-controlled Switching Effect in Amorphous Semiconductors," J. Non-Cryst. Solids, 8-10, 408-414, 1972.			
**	CV3	Haifz, et al., "Effect of Composition on the Structure and Electrical Properties of As-Se-Cu Glasses," J. Apply. Phys., 54, 1950-1954, 1983.			
**	CW3	Hajto, et al., "Quantization Effects in Metal/a-Si:H/metal Devices," Int. J. Electronics, 73, 911-913, 1992.			
**	CX3	Hajto, et al., "DC and AC Measurements on Metal/a-Si:H/metal Room Temperature Quantised Resistance Devices," J. Non-Cryst. Solids, 266-269, 1058-1061, 2000.			
**	CY3	Hajto, et al., "Theory of Room Temperature Quantized Resistance Effects in Metal-a-Si:H-metal Thin Film Structures," J. Non-Cryst. Solids, 198-200, 825-828, 1996.			
**	CZ3	Hajto, et al., "Analogue Memory and Ballistic Electron Effects in Metal-amorphous Silicon Structures," Phil. Mag. B 63, 349-369, 1991.			
**	CA4	Hayashi, et al., "Polarized Memory Switching in Amorphous Se Film," Japan. J. Appl. Phys., 13, 1163-1164, 1974.			
**	CB4	Hegab, et al., "Memory Switching Phenomena in Thin Films of Chalcogenide Semiconductors," Vacuum, 45, 459-462, 1994.			
**	CC4	Hong, et al., "Switching Behavior in II-IV-V2 Amorphous Semiconductor Systems," J. Non-Cryst. Solids, 116, 191-200, 1990.			
**	CD4	Gosain, et al., "Nonvolatile Memory Based on Reversible Phase Transition Phenomena in Telluride Glasses," Jap. J. Appl. Phys., 28, 1013-1018, 1989.			
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**	CI4	Haifz, et al., "Effect of Composition on the Structure and Electrical Properties of As-Se-Cu Glasses," J. Apply. Phys., 54, 1950-1954, 1983.			
** Lee	CJ4	Hajto, et al., "Quantization Effects in Metal/a-Si:H/metal Devices," Int. J. Electronics, 73, 911-913, 1992.			

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Lee	CL4	Hajto, et al., "Theory of Room Temperature Quantized Resistance Effects in Metal-a-Si:H-metal Thin Film Structures," J. Non-Cryst. Solids, 198-200, 825-828, 1996.				
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Lee	CY4	Hajto, et al., "Theory of Room Temperature Quantized Resistance Effects in Metal-a-Si:H-metal Thin Film Structures," J. Non-Cryst. Solids, 198-200, 825-828, 1996.				
Lee	CZ4	Hajto, et al., "Analogue Memory and Ballistic Electron Effects in Metal-amorphous Silicon Structures," Phil. Mag. B 63, 349-369, 1991.				
Lee	CA5	Hayashi, et al., "Polarized Memory Switching in Amorphous Se Film," Japan. J. Appl. Phys., 13, 1163-1164, 1974.				
Lee	CB5	Hegab, et al., "Memory Switching Phenomena in Thin Films of Chalcogenide Semiconductors," Vacuum, 45, 459-462, 1994.				
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Lee	CE5	Hu, et al., "Constant Current Forming in Cr/p+a-Si:H/V Thin Film Devices," J. Non-Cryst. Solids, 227-230, 1187-1191, 1998.				
**	CF5	Hu, et al., "Capacitance Anomaly Near the Metal-non-metal Transition in Cr-hydrogenated Amorphous Si-V Thin-film Devices," Phil. Mag. B, 74, 37-50, 1996.				
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**	CH5	Iizima, et al., "Electrical and Thermal Properties of Semiconducting Glasses As-Te-Ge," Solid State Comm. 8, 153-155, 1970.				
**	CI5	Ishikawa, et al., "Photovoltaic Study on the Photo-enhanced Diffusion of Ag in Amorphous Films of Ge2S3," J. Non-Cryst. Solids, 35 & 36, 1061-1066, 1980.				
**	CJ5	Iyetomi, et al., "Incipient Phase Separation in Ag/Ge/Se Glasses: Clustering of Ag Atoms," J. Non-Cryst. Solids, 262, 135-142, 2000.				
**	CK5	Jones, et al., "Switching Properties of Thin Selenium Films Under Pulsed Bias," Thin Solid Films, 40, L15-L18, 1977.				
**	CL5	Joullie, et al., "On the DC Electrical Conduction of Amorphous As2Se7 Before Switching," Phys. Stat. Sol. (a) 13, K105-K109, 1972.				
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**	CN5	Kaplan, et al., "Electrothermal Switching in Amorphous Semiconductors," J. Non-Cryst. Solids, 8-10, 538-543, 1972.				
**	CO5	Kawaguchi, et al., "Analysis of Change in Optical Transmission Spectra Resulting from Ag Photodoping in Chalcogenide Film," Jpn. J. Appl. Phys., 26, 15-21, 1987.				
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**	CQ5	Kolobov, "On the Origin of P-type Conductivity in Amorphous Chalcogenides," J. Non-Cryst. Solids, 198-200, 728-731, 1996.				
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Lee	CZ5	Matsushita, et al., "Polarized Memory Effect Observed on Amorphous Selenium Thin Films," Jpn. J. Appl. Phys., 11, 606, 1972.			
**	CA6	Mazurier, et al., "Reversible and Irreversible Electrical Switching in TeO ₂ -V ₂ O ₅ Based Glasses," Journal de Physique IV 2, C2-185 - C2-188, 1992.			
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**	CF6	Miyatani, "Ionic Conduction in Beta-Ag ₂ Te and Beta-Ag ₂ Se," Journal Phys. Soc. Japan, 14, 996-1002, 1959.			
**	CG6	Mott, "Conduction in Glasses Containing Transition Metal Ions," J. Non-Cryst. Solids, 1, 1-17, 1968.			
**	CH6	Nakayama, et al., "Nonvolatile Memory Based on Phase Transitions in Chalcogenide Thin Films," Jpn. J. Appl. Phys., 32, 564-569, 1993.			
**	CI6	Nakayama, et al., "Submicron Nonvolatile Memory Cell Based on Reversible Phase Transition in Chalcogenide Glasses," Jpn. J. Appl. Phys., 39, 6157-6161, 2000.			
**	CJ6	Nang, et al., "Electrical and Optical Parameters of Ge _x Se _{1-x} Amorphous Thin Films," Jap. J. App. Phys., 15, 849-853, 1976.			
**	CK6	Narayanan, et al., "Evidence Concerning the Effect of Topology on Electrical Switching in Chalcogenide Network Glasses," Phys. Rev. B, 54, 4413-4415, 1996.			
**	CL6	Neale, et al., "The Application of Amorphous Materials to Computer Memories," IEEE transactions on electron dev. Ed-20, 195-209, 1973.			
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				Application Number	Not Yet Assigned 10/777,684
				Filing Date	Concurrently Herewith
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	13	of	14	Attorney Docket Number	M4065.0699/P699-B

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
Lee	CR6	Pearson, et al., "Filamentary Conduction in Semiconducting Glass Diodes," App. Phys. Lett., 14, 280-282, 1969.				
**	CS6	Pinto, et al., "Electric Field Induced Memory Switching in Thin Films of the Chalcogenide System Ge-As-Se," Appl. Phys. Lett., 19, 221-223, 1971.				
**	CT6	Popescu, "The Effect of Local Non-uniformities on Thermal Switching and High Field Behavior of Structures with Chalcogenide Glasses," Solid-state Electronics, 18, 671-681, 1975.				
**	CU6	Popescu, et al., "The Contribution of the Lateral Thermal Instability to the Switching Phenomenon," J. Non-Cryst. Solids, 8-10, 531-537, 1972.				
**	CV6	Popov, et al., "Memory and Threshold Switching Effects in Amorphous Selenium," Phys. Stat. Sol. (a) 44, K71-K73, 1977.				
**	CW6	Prakash, et al., "Easily Reversible Memory Switching in Ge-As-Te Glasses," J. Phys. D: Appl. Phys., 29, 2004-2008, 1996.				
**	CX6	Rahman, et al., "Electronic Switching in Ge-Bi-Se-Te Glasses," Mat. Sci. and Eng. B12, 219-222, 1992.				
**	CY6	Ramesh, et al., "Electrical Switching in Germanium Telluride Glasses Doped With Cu and Ag," Appl. Phys. A 69, 421-425, 1999.				
**	CZ6	Rose, et al., "Amorphous Silicon Analogue Memory Devices," J. Non-Cryst. Solids, 115, 168-170, 1989.				
**	CA7	Rose, et al., "Aspects of Non-volatility in a -Si:H Memory Devices," Mat. Res. Soc. Symp. Proc. V 258, 1075-1080, 1992.				
**	CB7	Schuocker, et al., "On the Reliability of Amorphous Chalcogenide Switching Devices," J. Non-Cryst. Solids, 29, 397-407, 1978.				
**	CC7	Sharma, et al., "Electrical Conductivity Measurements of Evaporated Selenium Films in Vacuum," Proc. Indian Natn. Sci. Acad. 46, A, 362-368, 1980.				
**	CD7	Sharma, "Structural, Electrical and Optical Properties of Silver Selenide Films," Ind. J. Of Pure and Applied Phys., 35, 424-427, 1997.				
**	CE7	Snell, et al., "Analogue Memory Effects in Metal/a-Si:H/metal Memory Devices," J. Non-Cryst. Solids, 137-138, 1257-1262, 1991.				
**	CF7	Snell, et al., "Analogue Memory Effects in Metal/a-Si:H/metal Thin Film Structures," Mat. Res. Soc. Symp. Proc. V 297, 1017-1021, 1993.				
**	CG7	Steventon, "Microfilaments in Amorphous Chalcogenide Memory Devices," J. Phys. D: Appl. Phys., 8, L120-L122, 1975.				
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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				Art Unit	N/A 2823
				Examiner Name	Not Yet Assigned H. LEE
Sheet	14	of	14	Attorney Docket Number	M4065.0699/P699-B

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Lee	CJ7	Tanaka, "Ionic and Mixed Conductions in Ag Photodoping Process," Mod. Phys. Lett B 4, 1373-1377, 1990.			T ²
Lee	CK7	Tanaka, et al., "Thermal Effects on Switching Phenomenon in Chalcogenide Amorphous Semiconductors," Solid State Comm., 8, 387-389, 1970.			
Lee	CL7	Thornburg, "Memory Switching in a Type I Amorphous Chalcogenide," J. Elect. Mat., 2, 3-15, 1973.			
Lee	CM7	Thornburg, "Memory Switching in Amorphous Arsenic Triselenide," J. Non-Cryst. Solids, 11, 113-120, 1972.			
Lee	CN7	Thornburg, et al., "Electric Field Enhanced Phase Separation and Memory Switching in Amorphous Arsenic Triselenide," Journal(??), 4609-4612, 1972.			
Lee	CO7	Tichy, et al., "Remark on the Glass-forming Ability in Ge _x Se _{1-x} and As _x Se _{1-x} Systems," J. Non-Cryst. Solids, 261, 277-281, 2000.			
Lee	CP7	Titus, et al., "Electrical Switching and Short-range Order in As-Te Glasses," Phys. Rev. B 48, 14650-14652, 1993.			
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Lee	CR7	Tregouet, et al., "Silver Movements in Ag ₂ Te Thin Films: Switching and Memory Effects," Thin Solid Films, 57, 49-54, 1979.			
Lee	CS7	Uemura, et al., "Thermally Induced Crystallization of Amorphous Ge _{0.4} Se _{0.6} ," J. Non-Cryst. Solids, 117-118, 219-221, 1990.			
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Lee	CV7	Vodenicharov, et al., "Electrode-limited Currents in the Thin-film M-GeSe-M System," Mat. Chem. And Phys., 21, 447-454, 1989.			
Lee	CW7	Wang, et al., "High-performance Metal/silicide Antifuse," IEEE Electron Dev. Lett., 13, 471-472, 1992.			
Lee	CX7	Weirauch, "Threshold Switching and Thermal Filaments in Amorphous Semiconductors," App. Phys. Lett., 16, 72-73, 1970.			
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Lee	CZ7	Zhang, et al., "Variation of Glass Transition Temperature, T _g , With Average Coordination Number, <m>, in Network Glasses: Evidence of a Threshold Behavior in the Slope dT _g /d<m> at the Rigidity Percolation Threshold (<m>=2.4)," J. Non-Cryst. Solids, 151, 149-154, 1992.			

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